imall

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832 Email & Skype: info@chipsmall.com Web: www.chipsmall.com Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



1 A, 1% Precision Very Low Dropout Voltage Regulator with Enable

The NCP706 is a Very Low Dropout Regulator which provides up to 1 A of load current and maintains excellent output voltage accuracy of 1% including line, load and temperature variations. The operating input voltage range from 2.4 V up to 5.5 V makes this device suitable for Li–ion battery powered products as well as post–regulation applications. The product is available in 2.1 V, 2.2 V, 2.95 V, 3.0 V and 3.3 V fixed output voltage options. NCP706 is fully protected against overheating and output short circuit.

Very small 8–pin XDFN8 1.6 x 1.2, 04P package makes the device especially suitable for space constrained portable applications such as tablets and smartphones.

Features

- Operating Input Voltage Range: 2.4 V to 5.5 V
- Fixed Output Voltage Options: 2.1 V, 2.2 V, 2.95 V, 3.0 V and 3.3 V Other Output Voltage Options Available on Request.
- Low Quiescent Current of Typ. 200 µA
- Very Low Dropout: 155 mV Max. at I_{OUT} = 1 A
- ±1% Accuracy Over Load/Line/Temperature
- High PSRR: 60 dB at 1 kHz
- Internal Soft-Start to Limit the Inrush Current
- Thermal Shutdown and Current Limit Protections
- Stable with a 4.7 µF Ceramic Output Capacitor
- Available in XDFN8 1.6 x 1.2, 04P 8-pin Package
- These are Pb–Free Devices

Typical Applications

- Tablets, Smartphones,
- Wireless Handsets, Portable Media Players
- Portable Medical Equipment
- Other Battery Powered Applications

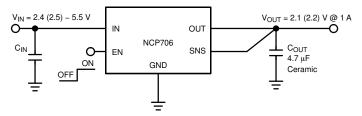


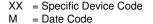
Figure 1. Typical Application Schematic



ON Semiconductor®

www.onsemi.com

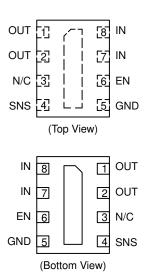




= Pb-Free Package

(Note: Microdot may be in either location)

PIN CONNECTION



ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 15 of this data sheet.

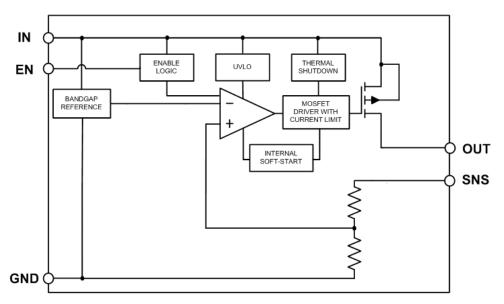


Figure 2. Simplified Internal Schematic Block Diagram

PIN FUNCTION DESCRIPTION

Pin No. XDFN8	Pin Name	Description			
1	OUT	Regulated output voltage. A minimum 4.7 µF ceramic capacitor is needed from this pin to ground to			
2	OUT	assure stability.			
3	3 N/C Not connected. This pin can be tied to ground to improve thermal dissipation.				
4	SNS	Remote sense connection. This pin should be connected to the output voltage rail.			
5	GND	Power supply ground.			
6	EN	Enable pin. Driving EN over 0.9 V turns on the regulator. Driving EN below 0.4 V puts the regulator into shutdown mode.			
7	IN	Input pin. A small capacitor is needed from this pin to ground to assure stability.			
8	IN]			
-	Exposed Pad	This pad enhances thermal performance and is electrically connected to GND. It is recommended that the exposed pad is connected to the ground plane on the board or otherwise left open.			

ABSOLUTE MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Input Voltage (Note 1)	V _{IN}	–0.3 V to 6 V	V
Output Voltage	V _{OUT}	–0.3 V to VIN + 0.3 V	V
Enable Input	V _{EN}	–0.3 V to VIN + 0.3 V	V
Output Short Circuit Duration	t _{SC}	Indefinite	s
Maximum Junction Temperature	T _{J(MAX)}	150	°C
Storage Temperature	T _{STG}	-55 to 150	°C
ESD Capability, Human Body Model (Note 2)	ESD _{HBM}	2000	V
ESD Capability, Machine Model (Note 2)	ESD _{MM}	200	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
Refer to ELECTRICAL CHARACTERISTIS and APPLICATION INFORMATION for Safe Operating Area.
This device series incorporates ESD protection and is tested by the following methods: ESD Human Body Model tested per EIA/JESD22-A114 Latch-up Current Maximum Rating tested per JEDEC standard: JESD78

THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Thermal Characteristics, XDFN8 1.6x1.2, 04P Thermal Resistance, Junction-to-Air	$R_{ hetaJA}$	160	°C/W

ELECTRICAL CHARACTERISTICS – VOLTAGE VERSION 2.1 V -40°C \leq T_J \leq 125°C; V_{IN} = V_{OUT(NOM)} + 0.3 V or 2.4 V, whichever is greater; I_{OUT} = 10 mA, C_{IN} = C_{OUT} = 4.7 μ F, V_{EN} = 0.9 V, unless otherwise noted. Typical values are at T_J = +25°C. (Note 3)

Parameter	Test Cor	nditions	Symbol	Min	Тур	Max	Unit
Operating Input Voltage			V _{IN}	2.4		5.5	V
Undervoltage lock-out	V _{IN} rising	UVLO	1.2	1.6	1.9	V	
Output Voltage Accuracy	$V_{OUT} + 0.3 \ V \le V_{IN} \le 4$.5 V, I _{OUT} = 0 – 1 A	V _{OUT}	2.079	2.10	2.121	V
Line Regulation	$V_{OUT} + 0.3 \ V \le V_{IN} \le 4$.5 V, I _{OUT} = 10 mA	Reg _{LINE}		2		mV
Load Regulation	$I_{OUT} = 0 \text{ mA to } 1 \text{ A}$		Reg _{LOAD}		2		mV
Load Transient	I_{OUT} = 10 mA to 1A or C_{OUT} = 10 μ F	10 mA to 1 A in 10 μs,	Tran _{LOAD}		±120		mV
Dropout voltage (Note 4)	$I_{OUT} = 1 \text{ A}, V_{OUT(nom)} =$	= 2.1 V	V _{DO}			300	mV
Output Current Limit	V _{OUT} = 90% V _{OUT(nom})	I _{CL}	1.1			А
Quiescent current	I _{OUT} = 0 mA		ا _Q		180	230	μΑ
Ground current	I _{OUT} = 1 A		I _{GND}		200		μA
Shutdown current	$V_{EN} \leq 0$ V, V_{IN} = 2.0 to 5.5 V				0.1	1	μΑ
Reverse Leakage Current in Shutdown	$V_{IN} = 5.5 V, V_{OUT} = V_{C}$ $V_{EN} < 0.4 V$	$\label{eq:VIN} \begin{array}{l} V_{IN} = 5.5 \ V, \ V_{OUT} = V_{OUT(NOM)}, \\ V_{EN} < 0.4 \ V \end{array}$			1.5	5	μΑ
EN Pin High Threshold EN Pin Low Threshold	V _{EN} Voltage increasing V _{EN} Voltage decreasing		V _{EN_HI} V _{EN_LO}	0.9		0.4	V V
EN Pin Input Current	V _{EN} = 5.5 V		I _{EN}		100	500	nA
Turn–on Time	$C_{OUT} = 4.7 \ \mu$ F, from assertion EN pin t	o 98% V _{out(nom)}	t _{ON}		200		μs
Power Supply Rejection Ratio	$ \begin{array}{ll} V_{IN} = 2.6 \ V, & f = 100 \ Hz \\ V_{OUT} = 2.1 \ V & f = 1 \ \text{kHz} \\ I_{OUT} = 0.5 \ \text{A} & f = 10 \ \text{kHz} \end{array} $		PSRR		60 60 40		dB
Output Noise Voltage	V _{OUT} = 2.1 V, V _{IN} = 2.6 V, I _{OUT} = 0.5 A f = 100 Hz to 100 kHz		V _{NOISE}		280		μV_{rms}
Thermal Shutdown Temperature	Temperature increasing from $T_J = +25^{\circ}C$		T _{SD}		160		°C
Thermal Shutdown Hysteresis	Temperature falling from	m T _{SD}	T _{SDH}	-	20	-	°C

Performance guaranteed over the indicated operating temperature range by design and/or characterization production tested at T_J = T_A = 25°C. Low duty cycle pulse techniques are used during testing to maintain the junction temperature as close to ambient as possible.
 Characterized when Vout falls 100 mV below the regulated voltage at VIN = VOUT(NOM) + 0.3 V.

ELECTRICAL CHARACTERISTICS – VOLTAGE VERSION 2.2 V -40°C \leq T_J \leq 125°C; V_{IN} = V_{OUT(NOM)} + 0.3 V or 2.5 V, whichever is greater; I_{OUT} = 10 mA, C_{IN} = C_{OUT} = 4.7 μ F, V_{EN} = 0.9 V, unless otherwise noted. Typical values are at T_J = +25°C. (Note 5)

Parameter	Test Conditions		Symbol	Min	Тур	Max	Unit
Operating Input Voltage			VIN	2.5		5.5	V
Undervoltage lock-out	V _{IN} rising		UVLO	1.2	1.6	1.9	V
Output Voltage Accuracy	$V_{OUT} + 0.3 \text{ V} \leq V_{IN} \leq 4.5 \text{ V},$	I _{OUT} = 0 – 1 A	Vout	2.178	2.2	2.222	V
Line Regulation	$V_{OUT} + 0.3 \text{ V} \leq V_{IN} \leq 4.5 \text{ V},$	I _{OUT} = 10 mA	Reg _{LINE}		2		mV
Load Regulation	$I_{OUT} = 0 \text{ mA to } 1 \text{ A}$		Reg _{LOAD}		2		mV
Load Transient	$I_{OUT} = 10 \text{ mA to } 1\text{A or } 10 \text{ m}$ $C_{OUT} = 10 \mu\text{F}$	nA to 1 A in 10 μs,	Tran _{LOAD}		±120		mV
Dropout voltage (Note 6)	$I_{OUT} = 1 \text{ A}, V_{OUT(nom)} = 2.2$	2 V	Vdo			300	mV
Output Current Limit	V _{OUT} = 90% V _{OUT(nom)}	$V_{OUT} = 90\% V_{OUT(nom)}$					Α
Quiescent current	IOUT = 0 mA		lq		180	230	μA
Ground current	IOUT = 1 A		Ignd		200		μA
Shutdown current	$V_{EN} \le 0$ V, V_{IN} = 2.0 to 5.5 V				0.1	1	μA
EN Pin High Threshold EN Pin Low Threshold	V _{EN} Voltage increasing V _{EN} Voltage decreasing		V _{EN_HI} V _{EN_LO}	0.9		0.4	V
EN Pin Input Current	Ven = 5.5 V		I _{EN}		100	500	nA
Turn–on Time	$C_{OUT} = 4.7 \ \mu$ F, from assertive V _{out(nom)}	ion EN pin to 98%	t _{ON}		200		μs
Power Supply Rejection Ratio			PSRR		55 70 60		dB
Output Noise Voltage	V _{OUT} = 2.2 V, V _{IN} = 2.7 V, I _{OUT} = 0.5 A f = 100 Hz to 100 kHz		VNOISE		300		μV_{rms}
Thermal Shutdown Temperature	Temperature increasing from $T_J = +25^{\circ}C$		T _{SD}	1	160		°C
Thermal Shutdown Hysteresis	Temperature falling from Temperature falling for temperature falling for temperature falling for temperature falling for temperature falling falling falling falling falling for temperature falling	SD	T _{SDH}	-	20	-	°C

Performance guaranteed over the indicated operating temperature range by design and/or characterization production tested at T_J = T_A = 25°C. Low duty cycle pulse techniques are used during testing to maintain the junction temperature as close to ambient as possible.
 Characterized when V_{OUT} falls 100 mV below the regulated voltage at V_{IN} = V_{OUT(NOM)} + 0.3 V.

ELECTRICAL CHARACTERISTICS – VOLTAGE VERSION 2.95 V -40°C \leq T_J \leq 125°C; V_{IN} = V_{OUT(NOM)} + 0.3 V or 3.3 V, whichever is greater; I_{OUT} = 10 mA, C_{IN} = C_{OUT} = 4.7 μ F, V_{EN} = 0.9 V, unless otherwise noted. Typical values are at T_J = +25°C. (Note 7)

Parameter	Test Conditions	Symbol	Min	Тур	Max	Unit
Operating Input Voltage		V _{IN}	2.4		5.5	V
Undervoltage lock-out	V _{IN} rising, I _{OUT} = 0	UVLO	1.2	1.6	1.9	V
Output Voltage Accuracy	V_{OUT} + 0.3 V \leq V _{IN} \leq 4.5 V, I _{OUT} = 0 - 1 A	V _{OUT}	2.9205	2.95	2.9795	V
Line Regulation	V_{OUT} + 0.3 V \leq V_{IN} \leq 4.5 V, I_{OUT} = 10 mA	Reg _{LINE}		2		mV
Load Regulation	$I_{OUT} = 0$ mA to 1 A, $V_{IN} = 3.3$ V	Reg _{LOAD}		2		mV
Load Transient	I_{OUT} = 10 mA to 1 A in 10 $\mu s,$ V_{IN} = 3.5 V C_{OUT} = 10 μF	Tran _{LOAD}		±120		mV
Dropout voltage (Note 8)	I _{OUT} = 1 A, V _{OUT(nom)} = 3.0 V	V _{DO}		155	230	mV
Output Current Limit	V _{OUT} = 90% V _{OUT(nom)}	I _{CL}	1.1		1	А
Quiescent current	I _{OUT} = 0 mA	Ι _Q		170	230	μA
Ground current	I _{OUT} = 1 A	I _{GND}		200	1	μA
Shutdown current	$V_{EN} \leq 0$ V, $V_{IN} = 2.4$ to 5.5 V			0.1	1	μA
EN Pin High Threshold EN Pin Low Threshold	V _{EN} Voltage increasing V _{EN} Voltage decreasing	V _{EN_HI} V _{EN_LO}	0.9		0.4	V
EN Pin Input Current	V _{EN} = 5.5 V	I _{EN}		100	500	nA
Turn–on Time	C_{OUT} = 4.7 $\mu F,$ from assertion EN pin to 98% $V_{out(nom)}$	t _{ON}		150		μs
Power Supply Rejection Ratio	$ \begin{array}{ll} V_{IN} = 3.5 \ V + 200 \ mVpp & f = 100 \ Hz \\ modulation, \ V_{OUT} = 2.95 \ V & f = 1 \ kHz \\ I_{OUT} = 0.5 \ A, \ C_{OUT} = 4.7 \ \mu F & f = 10 \ kHz \end{array} $	PSRR		65 58 52		dB
Output Noise Voltage	V _{OUT} = 2.95 V, V _{IN} = 4.0 V, I _{OUT} = 0.5 A f = 100 Hz to 100 kHz	V _{NOISE}		300		μV_{rms}
Thermal Shutdown Temperature	Temperature increasing from $T_J = +25^{\circ}C$	T _{SD}		160	1	°C
Thermal Shutdown Hysteresis	Temperature falling from T _{SD}	T _{SDH}	-	20	_	°C

7. Performance guaranteed over the indicated operating temperature range by design and/or characterization production tested at T_J = T_A = 25° C. Low duty cycle pulse techniques are used during testing to maintain the junction temperature as close to ambient as possible. 8. Characterized when V_{OUT} falls 90 mV below the regulated voltage at V_{IN} = 3.3 V, I_{OUT} = 10 mA.

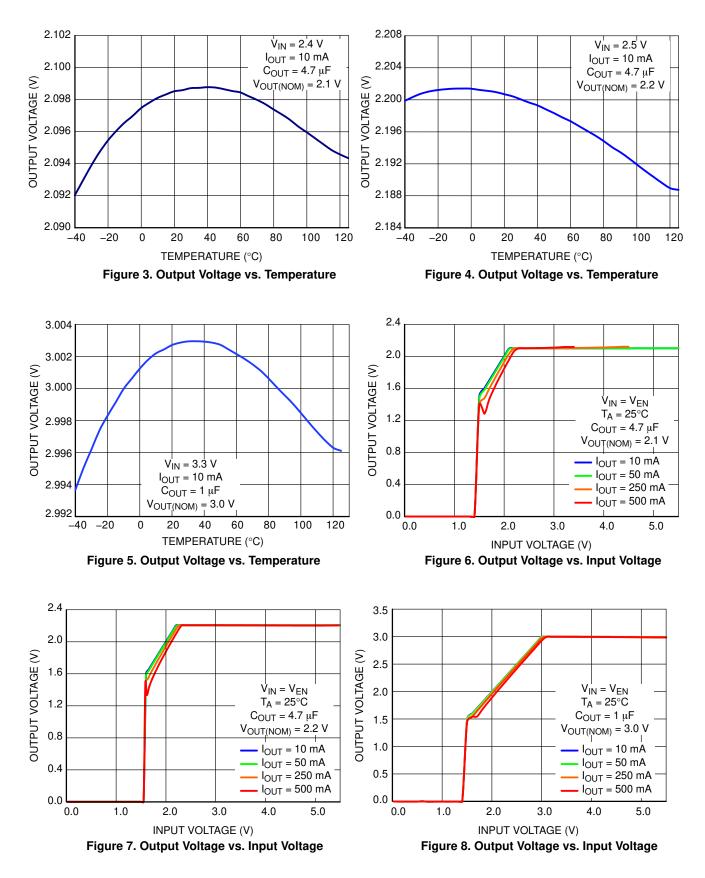
ELECTRICAL CHARACTERISTICS – VOLTAGE VERSION 3.0 V

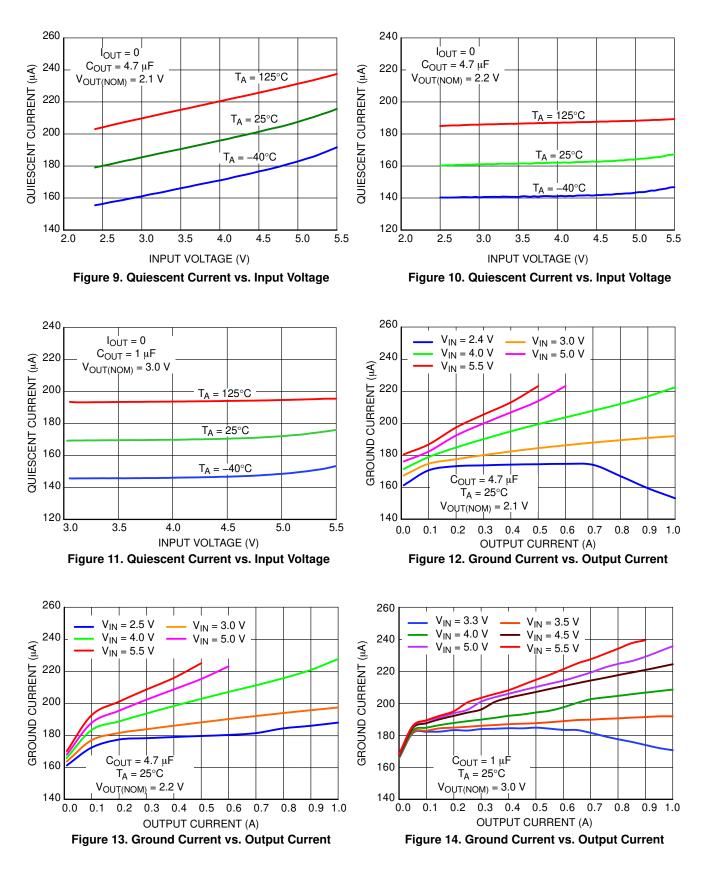
 $-40^{\circ}C \le T_J \le 125^{\circ}C; V_{IN} = V_{OUT(NOM)} + 0.3 \text{ V or } 3.3 \text{ V}, \text{ whichever is greater}; I_{OUT} = 10 \text{ mA}, C_{IN} = C_{OUT} = 4.7 \text{ } \mu\text{F}, V_{EN} = 0.9 \text{ V}, \text{ unless otherwise noted}. Typical values are at T_J = +25^{\circ}C. (Note 9)$

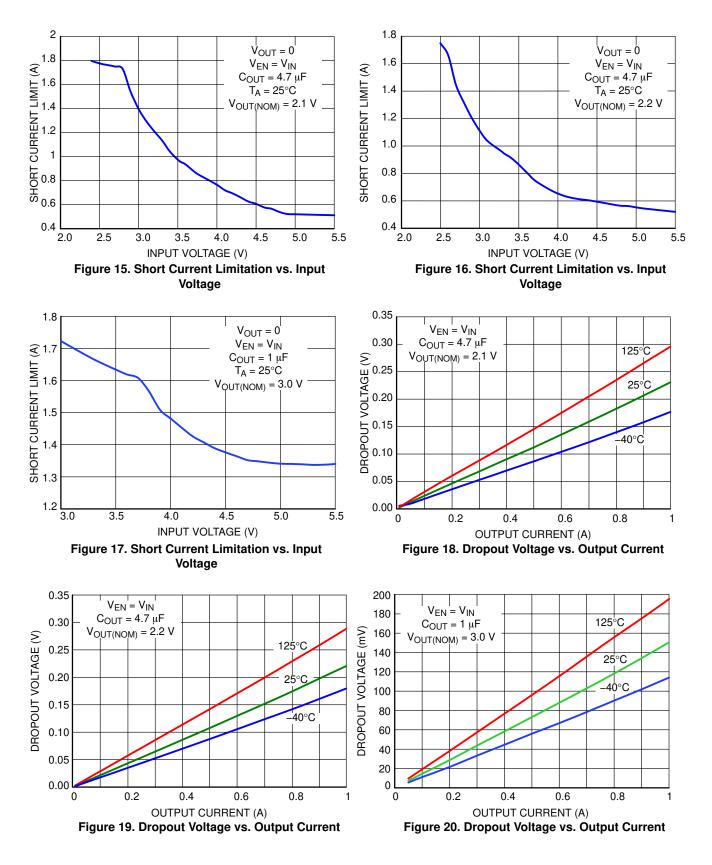
Parameter	Test Conditions	Symbol	Min	Тур	Max	Unit
Operating Input Voltage		V _{IN}	2.4		5.5	V
Undervoltage lock-out	V _{IN} rising, I _{OUT} = 0	UVLO	1.2	1.6	1.9	V
Output Voltage Accuracy	$V_{OUT} + 0.3 \text{ V} \leq V_{IN} \leq 4.5 \text{ V}, I_{OUT} = 0 - 1 \text{ A}$	V _{OUT}	2.97	3.0	3.03	V
Line Regulation	V_{OUT} + 0.3 V \leq V_{IN} \leq 4.5 V, I_{OUT} = 10 mA	Reg _{LINE}		2		mV
Load Regulation	$I_{OUT} = 0$ mA to 1 A, $V_{IN} = 3.3$ V	Reg _{LOAD}		2		mV
Load Transient	I_{OUT} = 10 mA to 1 A in 10 $\mu s,V_{IN}$ = 3.5 V C_{OUT} = 10 μF	Tran _{LOAD}		±120		mV
Dropout voltage (Note 10)	I _{OUT} = 1 A, V _{OUT(nom)} = 3.0 V	V _{DO}		155	230	mV
Output Current Limit	V _{OUT} = 90% V _{OUT(nom)}	I _{CL}	1.1			А
Quiescent current	I _{OUT} = 0 mA	Ι _Q		170	230	μΑ
Ground current	I _{OUT} = 1 A	I _{GND}		200		μΑ
Shutdown current	$V_{EN} \leq 0$ V, $V_{IN} = 2.0$ to 5.5 V			0.1	1	μΑ
EN Pin High Threshold EN Pin Low Threshold	V _{EN} Voltage increasing V _{EN} Voltage decreasing	V _{EN_HI} V _{EN_LO}	0.9		0.4	V
EN Pin Input Current	V _{EN} = 5.5 V	I _{EN}		100	500	nA
Turn-on Time	C_{OUT} = 4.7 $\mu F,$ from assertion EN pin to 98% $V_{out(nom)}$	t _{ON}		150		μs
Power Supply Rejection Ratio	$ \begin{array}{ll} V_{IN} = 3.5 \ V + 200 \ mVpp & f = 100 \ Hz \\ modulation, \ V_{OUT} = 3.0 \ V & f = 1 \ kHz \\ I_{OUT} = 0.5 \ A, \ C_{OUT} = 4.7 \ \mu F & f = 10 \ kHz \end{array} $	PSRR		65 58 52		dB
Output Noise Voltage	$V_{OUT} = 3.0 \text{ V}, V_{IN} = 4.0 \text{ V}, I_{OUT} = 0.5 \text{ A}$ f = 100 Hz to 100 kHz	V _{NOISE}		300		μV _{rms}
Thermal Shutdown Temperature	Temperature increasing from $T_J = +25^{\circ}C$	T _{SD}		160	1	°C
Thermal Shutdown Hysteresis	Temperature falling from T _{SD}	T _{SDH}	-	20	-	°C

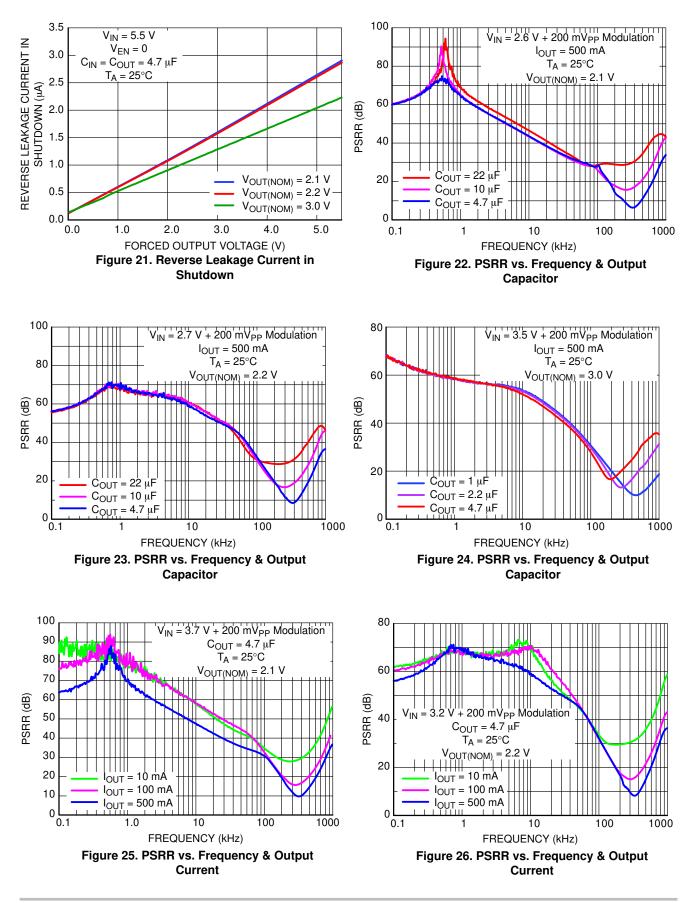
9. Performance guaranteed over the indicated operating temperature range by design and/or characterization production tested at $T_J = T_A = 25^{\circ}$ C. Low duty cycle pulse techniques are used during testing to maintain the junction temperature as close to ambient as possible. 10. Characterized when V_{OUT} falls 90 mV below the regulated voltage at V_{IN} = 3.3 V, I_{OUT} = 10 mA.

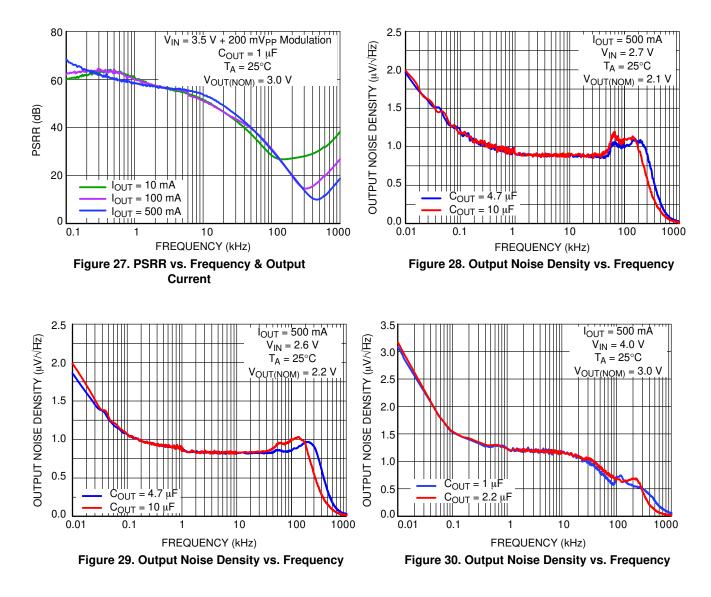
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.











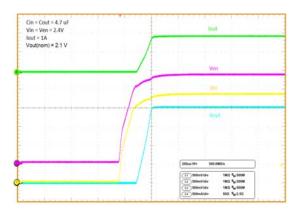


Figure 31. Turn-on by Coupled Input and Enable Pins

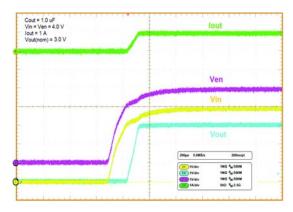


Figure 33. Turn-on by Coupled Input and Enable Pins

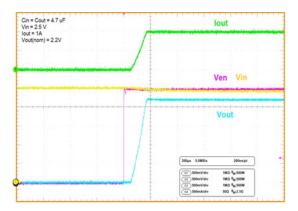


Figure 35. Turn-on by Enable Signal

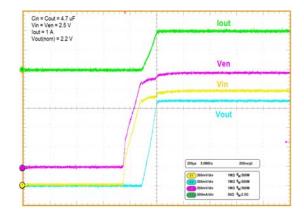


Figure 32. Turn-on by Coupled Input and Enable Pins

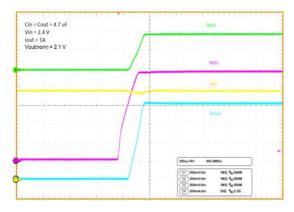


Figure 34. Turn-on by Enable Signal

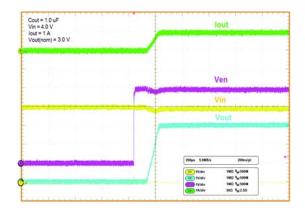


Figure 36. Turn-on by Enable Signal

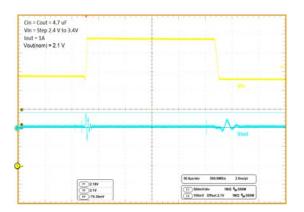


Figure 37. Line Transient Response

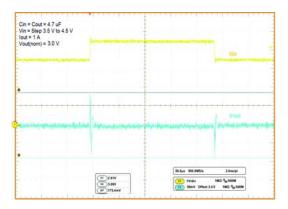


Figure 39. Line Transient Response

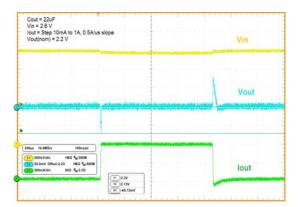


Figure 41. Load Transient Response

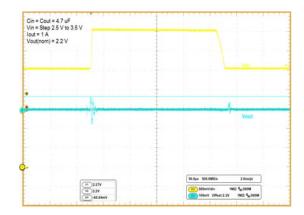


Figure 38. Line Transient Response

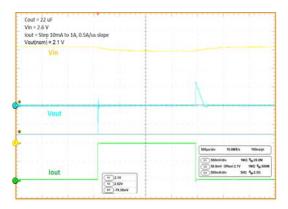


Figure 40. Load Transient Response

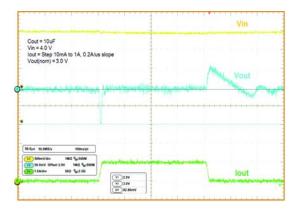


Figure 42. Load Transient Response

APPLICATIONS INFORMATION

Input Decoupling (Cin)

A 4.7 μ F capacitor either ceramic or tantalum is recommended and should be connected as close as possible to the pins of NCP706 device. Higher values and lower ESR will improve the overall line transient response.

Output Decoupling (Cout)

The minimum decoupling value for NCP706MX21TAG and NCP706MX22TAG devices is 4.7 μ F and can be augmented to fulfill stringent load transient requirements. The minimum decoupling value for NCP706MX295TAG and NCP706MX706300TAG devices is 1 μ F. The regulator accepts ceramic chip capacitors MLCC. If a tantalum capacitor is used, and its ESR is large, the loop oscillation may result. Larger values improve noise rejection and PSRR.

Enable Operation

The enable pin EN will turn on or off the regulator. These limits of threshold are covered in the electrical specification section of this data sheet. If the enable is not used then the pin should be connected to V_{IN} .

Hints

Please be sure the V_{in} and GND lines are sufficiently wide. If their impedance is high, noise pickup or unstable operation may result.

Set external components, especially the output capacitor, as close as possible to the circuit.

The sense pin SNS trace is recommended to be kept as far from noisy power traces as possible and as close to load as possible.

Thermal

As power across the NCP706 increases, it might become necessary to provide some thermal relief. The maximum power dissipation supported by the device is dependent upon board design and layout. Mounting pad configuration on the PCB, the board material, and also the ambient temperature affect the rate of temperature rise for the part. This is stating that when the NCP706 has good thermal conductivity through the PCB, the junction temperature will be relatively low with high power dissipation.

The power dissipation across the device can be roughly represented by the equation:

$$P_{D} = (V_{IN} - V_{OUT}) * I_{OUT} [W]$$
 (eq. 1)

The maximum power dissipation depends on the thermal resistance of the case and circuit board, the temperature differential between the junction and ambient, PCB orientation and the rate of air flow.

The maximum allowable power dissipation can be calculated using the following equation:

$$P_{MAX} = (T_J - T_A) / \theta_{JA} [W]$$
 (eq. 2)

Where $(T_J - T_A)$ is the temperature differential between the junction and the surrounding environment and θ_{JA} is the thermal resistance from the junction to the ambient.

Connecting the exposed pad and non connected pin 3 to a large ground pad or plane helps to conduct away heat and improves thermal relief.

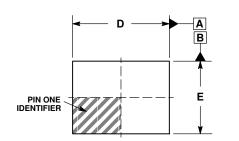
Device	Nominal Ooutput Voltage	Marking	Package	Shipping [†]
NCP706MX21TAG	2.1 V	QM	XDFN8 (Pb–Free)	3000 / Tape & Reel
NCP706MX22TAG	2.2 V	QR	XDFN8 (Pb–Free)	3000 / Tape & Reel
NCP706MX295TAG	2.95 V	A2	XDFN8 (Pb–Free)	3000 / Tape & Reel
NCP706MX300TAG	3.0 V	A3	XDFN8 (Pb–Free)	3000 / Tape & Reel
NCP706MX33TAG (In Development)	3.3 V	Q3	XDFN8 (Pb–Free)	3000 / Tape & Reel (Available Soon)

ORDERING INFORMATION

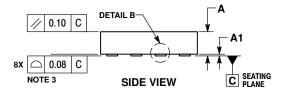
+ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

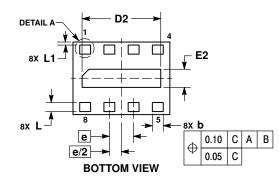
PACKAGE DIMENSIONS

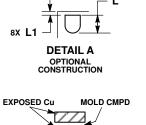
XDFN8 1.6x1.2, 0.4P CASE 711AS ISSUE D



TOP VIEW







DETAIL B OPTIONAL CONSTRUCTION

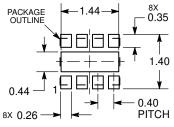
	DIM	MIN	NOM	MAX	
		MIL	LIMETE	RS	
	PAD A	S WELL	AS THE	TERMIN	ALS.
3.	COPL/	ANARITY	' APPLIE	S TO TH	E EXPOSED
2.	CONT	ROLLING	DIMEN:	SION: MI	LLIMETERS.
	ASME	Y14.5M,	1994.		

1. DIMENSIONING AND TOLERANCING PER

NOTES

WILLIWEIERS				
MIN NOM MAX				
0.300	0.375	0.450		
0.000	0.025	0.050		
0.130	0.180	0.230		
1.500	1.600	1.700		
1.200	1.300	1.400		
1.100	1.200	1.300		
0.200	0.300	0.400		
0.40 BSC				
0.150	0.200	0.250		
0.000	0.050	0.100		
	0.300 0.000 0.130 1.500 1.200 1.100 0.200 0.150	MIN NOM 0.300 0.375 0.000 0.025 0.130 0.180 1.500 1.600 1.200 1.300 1.100 1.200 0.300 0.300 0.40 BSG 0.150		

RECOMMENDED MOUNTING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and the intervent and the inter

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303–675–2175 or 800–344–3860 Toll Free USA/Canada Fax: 303–675–2176 or 800–344–3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support:

Phone: 421 33 790 2910 Japan Customer Focus Center Phone: 81–3–5817–1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative